



제 31회 한국반도체학술대회

The 31st Korean Conference on Semiconductors

2024년 1월 24일(수)-26일(금) | 경주화백컨벤션센터(HICO)

2024년 1월 26일(금), 13:45-15:30

Room E(105), 1층

E. Compound Semiconductors 분과

[FE2-E] Compound Semiconductor - GaN HEMTs

좌장: 김동현 박사(한국나노기술원)

초청발표 FE2-E-1 13:45-14:15	The GaN HEMT Technology for beyond 5G and Energy Applications June Sik Kwak RFHIC Inc
FE2-E-2 14:15-14:30	$L_g = 50$ nm AlGaIn/GaN HEMTs on 4-inch SiC with $f_{max} > 300$ GHz Wan-Soo Park ¹ , Hyo-Jin Kim ¹ , Hyeok-Jun Lee ¹ , Sang-Kuk Kim ² , Jacob Yun ² , Ted Kim ² , Jae-Hak Lee ¹ , Kyoungsoon Yang ³ , and Dae-Hyun Kim ¹ ¹ Kyungpook National University, ² QSI, ³ KAIST
FE2-E-3 14:30-14:45	Buffer-related Dynamic On-resistance Characteristics in AlGaIn/GaN-on-Si Structures Hyun-Seop Kim Kunsan National University
FE2-E-4 14:45-15:00	Thermal Management of GaN HEMTs through Electro-Thermal Modeling Changhwan Song ¹ , Sukwon Choi ² , and Jungwan Cho ¹ ¹ School of Mechanical Engineering, Sungkyunkwan University, ² Department of Mechanical Engineering, The Pennsylvania State University
FE2-E-5 15:00-15:15	Characterization of AlGaIn/GaN HEMTs on 4-inch SiC Substrate at Cryogenic Temperature Hyeok-Jun Lee ¹ , Wan-Soo Park ¹ , Hyo-Jin Kim ¹ , Jae-Hak Lee ¹ , Kyoungsoon Yang ² , and Dae-Hyun Kim ¹ ¹ Kyungpook National University, ² KAIST
FE2-E-6 15:15-15:30	p-GaN/p-AlGaIn/AlGaIn/GaN Heterojunction Field-effect Transistor with High Threshold Voltage Dong Guk Kim, Jun Hyeok Yim, Min Gi Jeong, Min Kuen Lee, and Ho Young Cha School of Electronic and Electrical Engineering, Hongik University